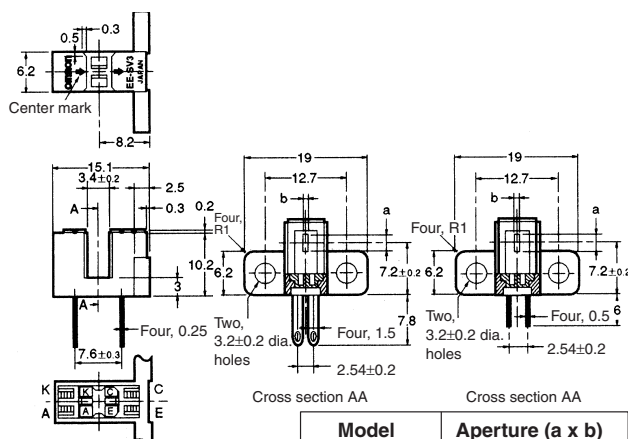


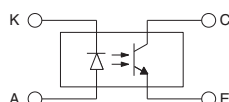
Photomicrosensor (Transmissive) EE-SV3 Series

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

Model	Aperture (a x b)
EE-SV3(-B)	2.1 x 0.5
EE-SV3-C(S)	2.1 x 1.0
EE-SV3-D(S)	2.1 x 0.2
EE-SV3-G(S)	0.5 x 2.1

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.2
3 < mm ≤ 6	±0.24
6 < mm ≤ 10	±0.29
10 < mm ≤ 18	±0.35
18 < mm ≤ 30	±0.42

■ Features

- High-resolution model with a 0.2-mm-wide or 0.5-mm-wide sensing aperture, high-sensitivity model with a 1-mm-wide sensing aperture, and model with a horizontal sensing aperture are available.
- Solder terminal models EE-SV3/-SV3-CS/-SV3-DS/-SV3-GS
- PCB terminal models EE-SV3-B/-SV3-C/-SV3-D/-SV3-G
- RoHS Compliant.

■ Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated value
Emitter	Forward current	I_F	50 mA (see note 1)
	Pulse forward current	I_{FP}	1 A (see note 2)
	Reverse voltage	V_R	4 V
Detector	Collector–Emitter voltage	V_{CEO}	30 V
	Emitter–Collector voltage	V_{ECO}	---
	Collector current	I_C	20 mA
	Collector dissipation	P_C	100 mW (see note 1)
Ambient temperature	Operating	T_{opr}	–25°C to 85°C
	Storage	T_{stg}	–30°C to 100°C
Soldering temperature		T_{sol}	260°C (see note 3)

Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

2. The pulse width is 10 μ s maximum with a frequency of 100 Hz.
3. Complete soldering within 10 seconds.

■ Ordering Information

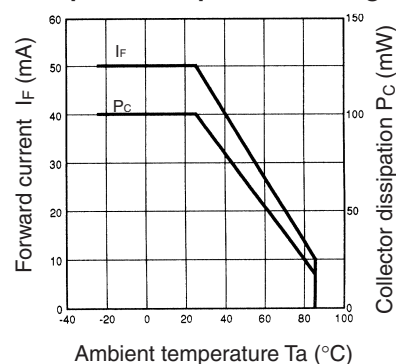
Description	Aperture (a x b)	Model
Photomicrosensor (transmissive)	2.1 x 0.5	EE-SV3-(B)
	2.1 x 1.0	EE-SV3-C(S)
	2.1 x 0.2	EE-SV3-D(S)
	0.5 x 2.1	EE-SV3-G(S)

■ Electrical and Optical Characteristics (Ta = 25°C)

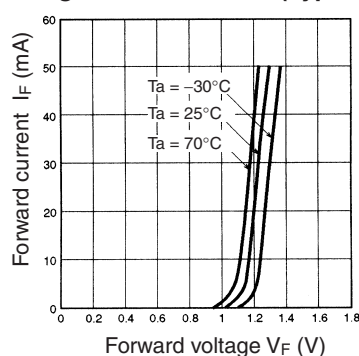
Item		Symbol	Value				Condition
			EE-SV3(-B)	EE-SV3-C(S)	EE-SV3-D(S)	EE-SV3-G(S)	
Emitter	Forward voltage	V _F	1.2 V typ., 1.5 V max.				I _F = 30 mA
	Reverse current	I _R	0.01 μA typ., 10 μA max.				V _R = 4 V
	Peak emission wavelength	λ _P	940 nm typ.				I _F = 20 mA
Detector	Light current	I _L	0.5 to 14 mA	1 to 28 mA	0.1 mA min.	0.5 to 14 mA	I _F = 20 mA, V _{CE} = 10 V
	Dark current	I _D	2 nA typ., 200 nA max.				V _{CE} = 10 V, 0 μA
	Leakage current	I _{LEAK}	---				---
	Collector–Emitter saturated voltage	V _{CE (sat)}	0.1 V typ., 0.4 V max.		---	0.1 V typ., 0.4 V max.	I _F = 20 mA, I _L = 0.1 mA
	Peak spectral sensitivity wavelength	λ _P	850 nm typ.				V _{CE} = 10 V
Rising time		tr	4 μs typ.				V _{CC} = 5 V,
Falling time		tf	4 μs typ.				R _L = 100 Ω, I _L = 5 mA

Engineering Data

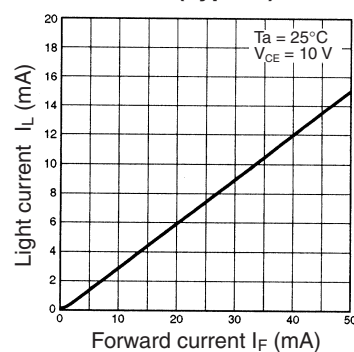
Forward Current vs. Collector Dissipation Temperature Rating



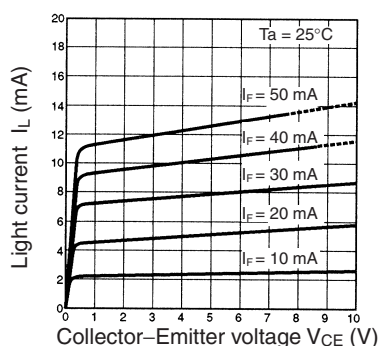
Forward Current vs. Forward Voltage Characteristics (Typical)



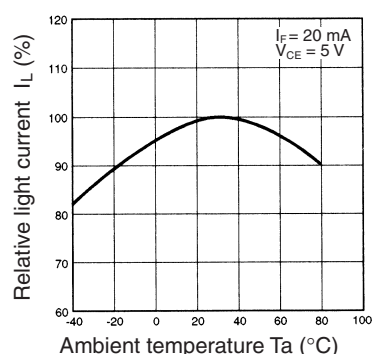
Light Current vs. Forward Current Characteristics (Typical)



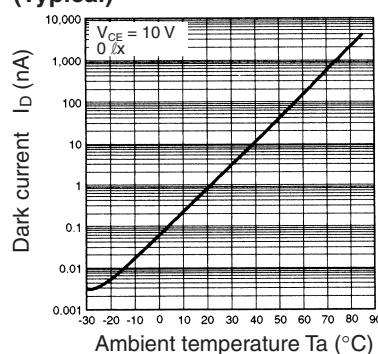
Light Current vs. Collector-Emitter Voltage Characteristics (EE-SV3-B)



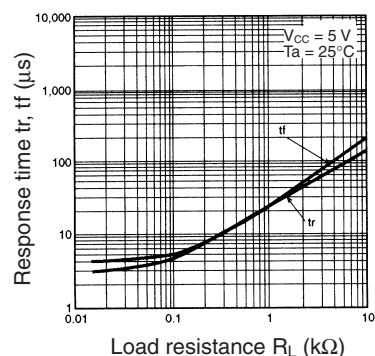
Relative Light Current vs. Ambient Temperature Characteristics (Typical)



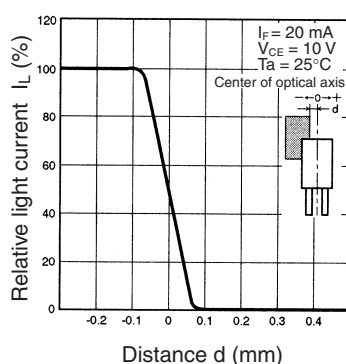
Dark Current vs. Ambient Temperature Characteristics (Typical)



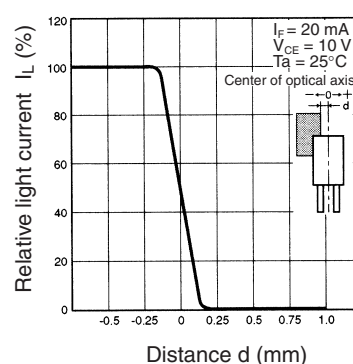
Response Time vs. Load Resistance Characteristics (Typical)



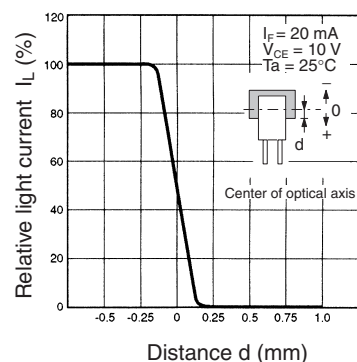
Sensing Position Characteristics (EE-SV3-D(S))



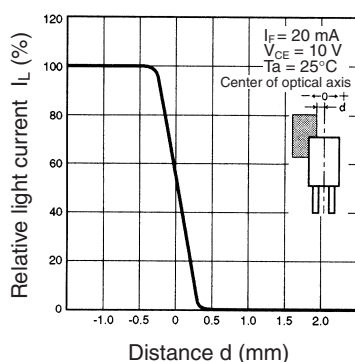
Sensing Position Characteristics (EE-SV3-B)



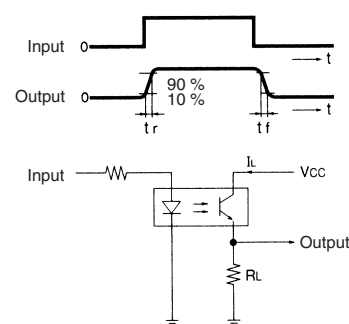
Sensing Position Characteristics (EE-SV3-G(S))

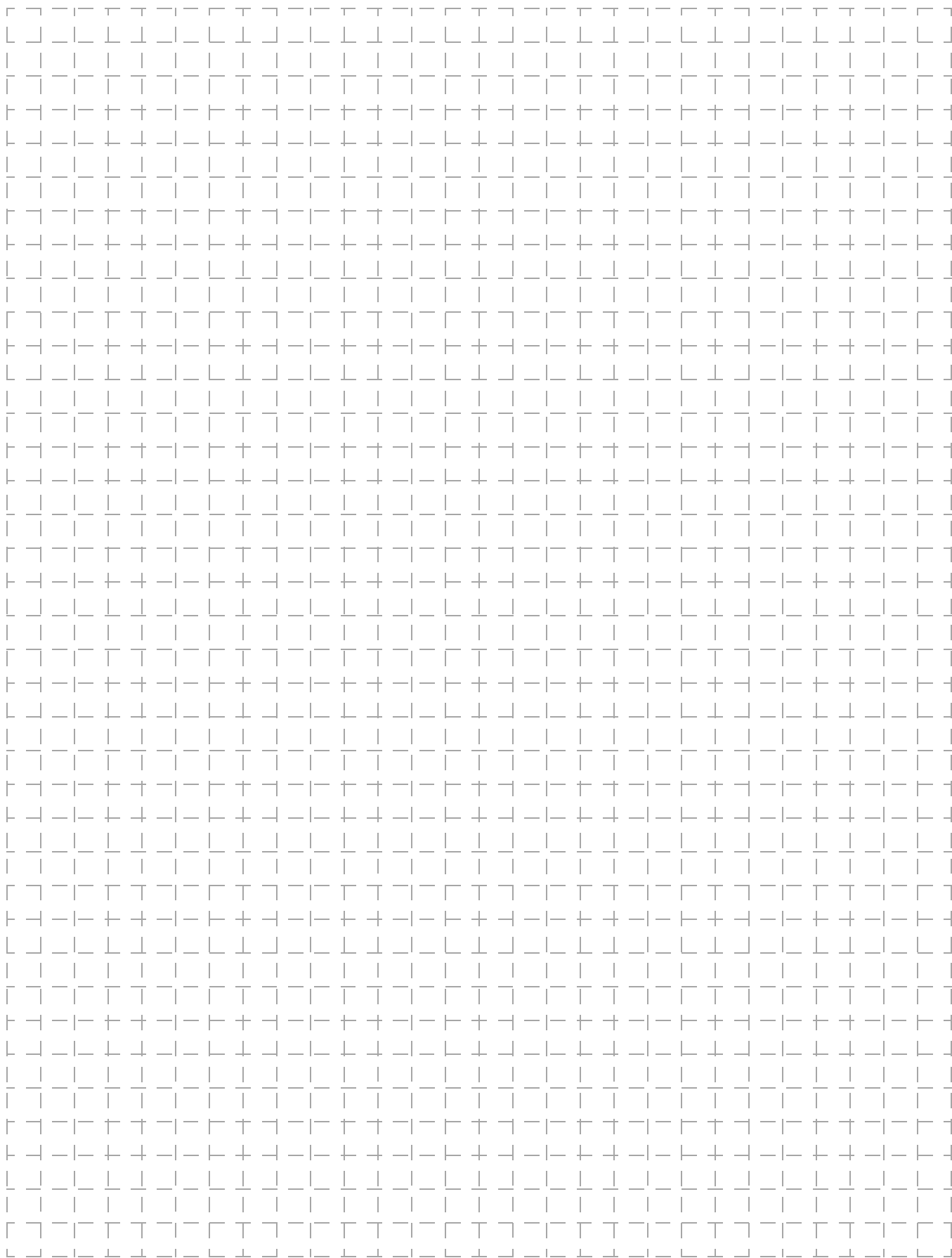


Sensing Position Characteristics (EE-SV3-C(S))



Response Time Measurement Circuit





All sales are subject to Omron Electronic Components LLC standard terms and conditions of sale, which can be found at http://www.components.omron.com/components/web/webfiles.nsf/sales_terms.html

ALL DIMENSIONS SHOWN ARE IN MILLIMETERS.

To convert millimeters into inches, multiply by 0.03937. To convert grams into ounces, multiply by 0.03527.

OMRON[®]

**OMRON ELECTRONIC
COMPONENTS LLC**

55 E. Commerce Drive, Suite B
Schaumburg, IL 60173

847-882-2288

OMRON ON-LINE

Global - <http://www.omron.com>

USA - <http://www.components.omron.com>